

THE MANUFACTURE OF ELECTRON EMITTERS USING MODIFIED PHOTSENSITIVE RESIN

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ABSTRACT

This study presents the experimental fabrication of electron emitters. The process involves two main steps. First, a two-photon lithography (2PL) system (IQnano3D, IQS nano) is employed to print the base structure along with the electrodes using a photosensitive resin (ResIQ, IQS nano). The resulting printed structures typically reach a height of approximately 50 μm . In the second step, these cured resin base structures undergo thermal treatment. This treatment transforms the surface of the resin into a conductive layer through heat-induced modification. The conductive layer may also be created via electroless plating or metal evaporation.

Each chip is fabricated on a square silicon substrate with dimensions of 10 $\times$ 10 mm, upon which the modified structures are formed. The emitter geometry is kept simple and the shapes have increased base area to provide good adhesion to the silicon substrate. Chips containing the conductive features were individually evaluated for outgassing in an ultra-high-vacuum chamber ($\sim 10^{-7}$ Pa) [1].

These chips are intended for testing and integration into low-energy electron optical systems, such as [2], with the aim of developing compact electron-emitting devices.

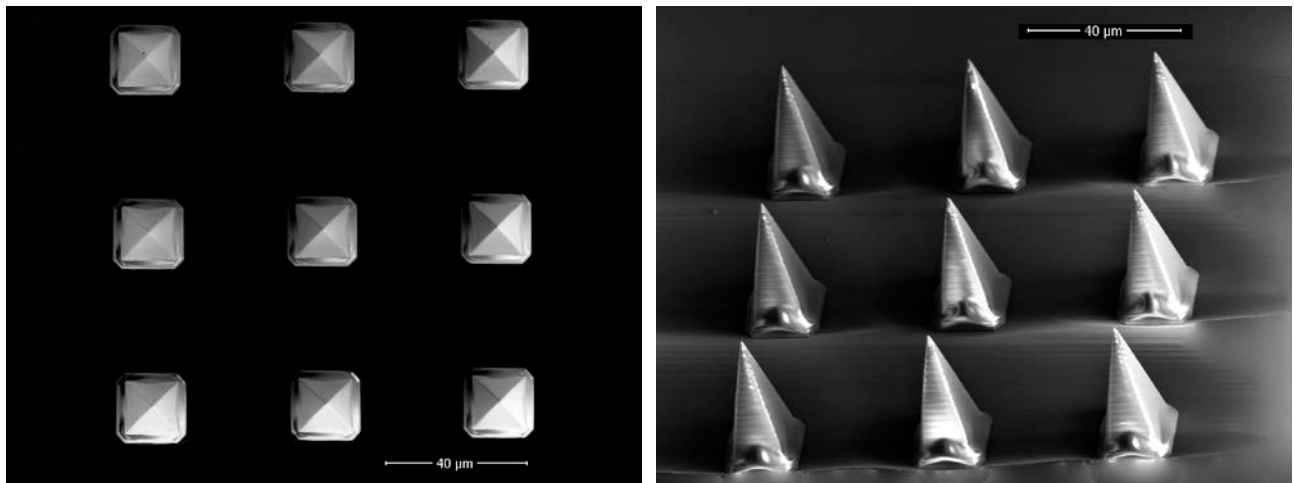


Fig. 1. a) SEM image of a pyramid-like array of fabricated resin-based emitter structures, left: top view, right: side view tilted by 30 degrees.

References

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